



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- $BV_{CEO} > 60V$
- $I_C = 7A$ Continuous Collector Current
- $I_{CM} = 12A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < 50mV @ 1A$
- $R_{CE(sat)} = 30m\Omega$
- h_{FE} Specified up to 7A for High Gain Hold Up
- Complementary PNP Type: NK-ZXTP19060CG

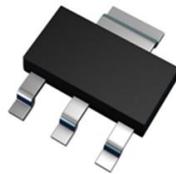
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 
- Weight: 0.112 grams (Approximate)

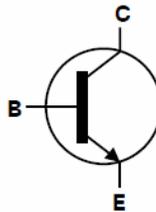
Applications

- Line Switching
- Motor Driving (including DC fans)
- High-Side Switches
- Lamp, Relay and Solenoid Drive

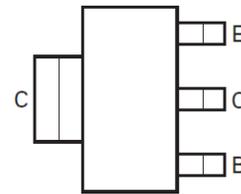
SOT223



Top View



Device Schematic



Pin-Out Top View

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	160	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	I _C	7	A
Peak Pulse Current	I _{CM}	12	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

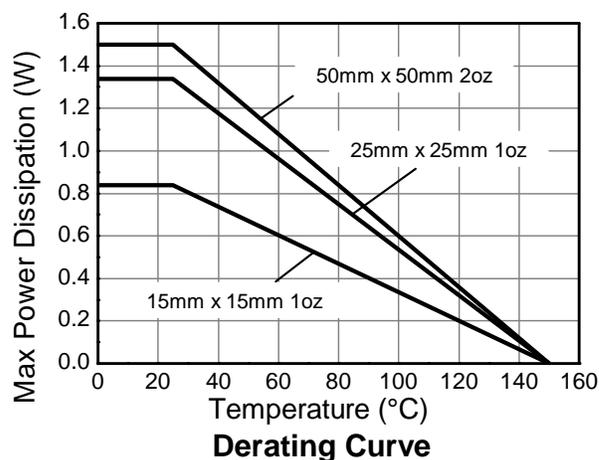
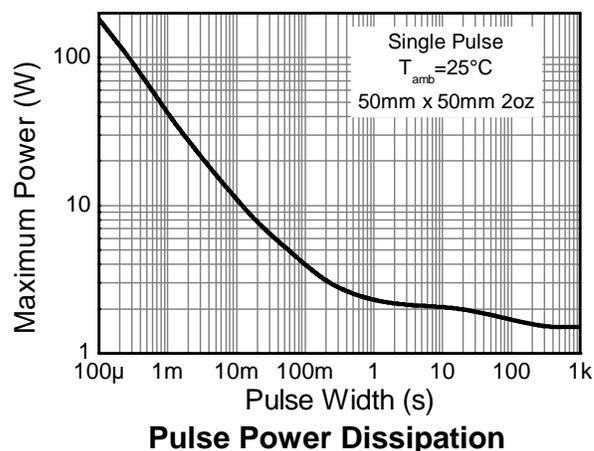
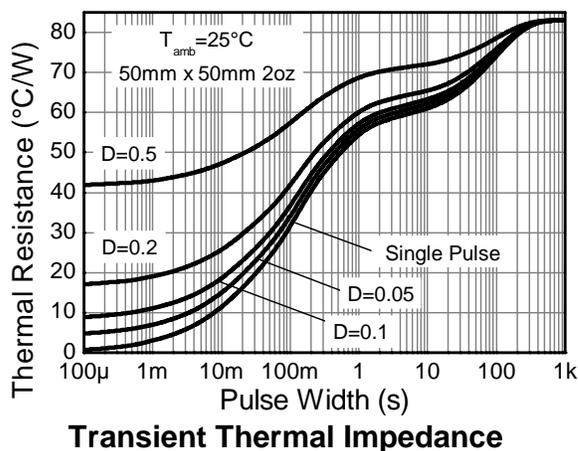
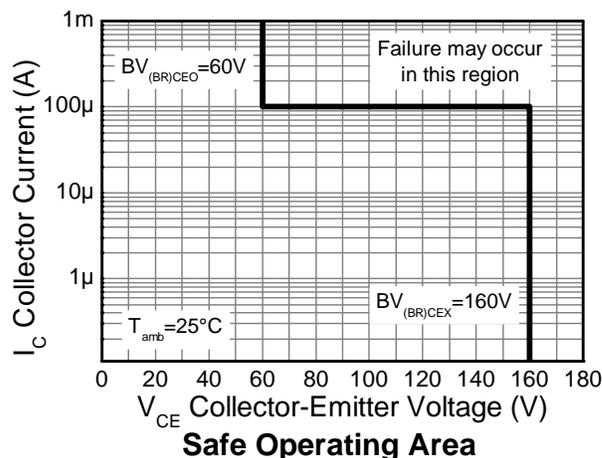
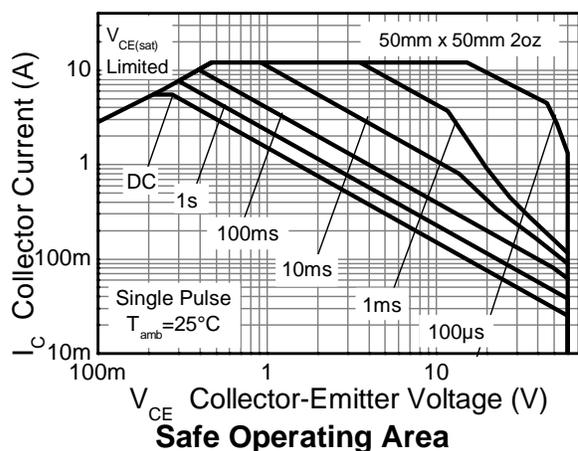
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	3.0	W
		24	
		1.6	
Thermal Resistance, Junction to Ambient	R _{θJA}	12.8	°C/W
		42	
		78	
Thermal Resistance, Junction to Lead	R _{θJL}	8.8	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

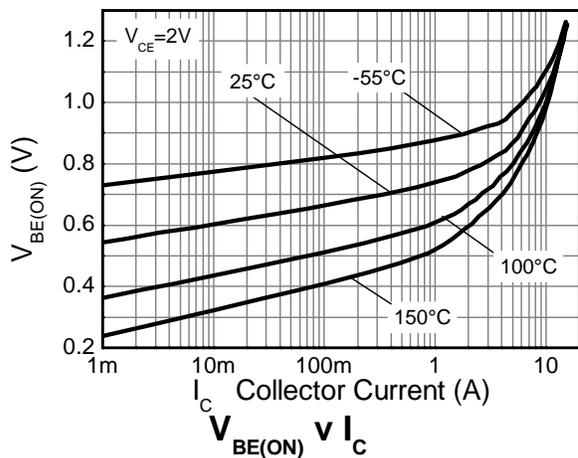
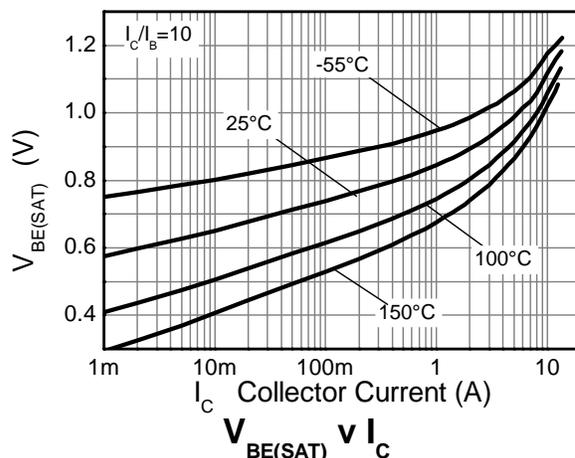
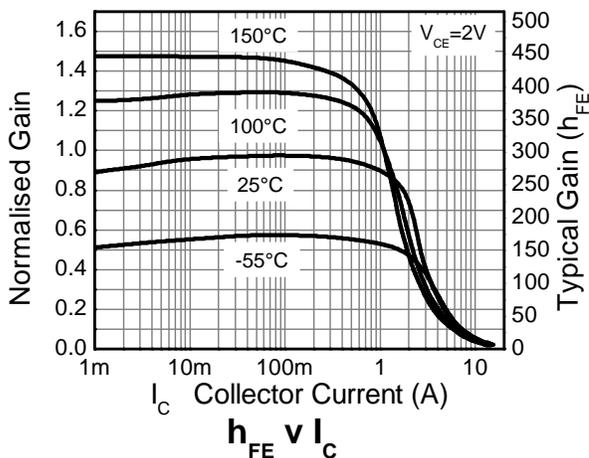
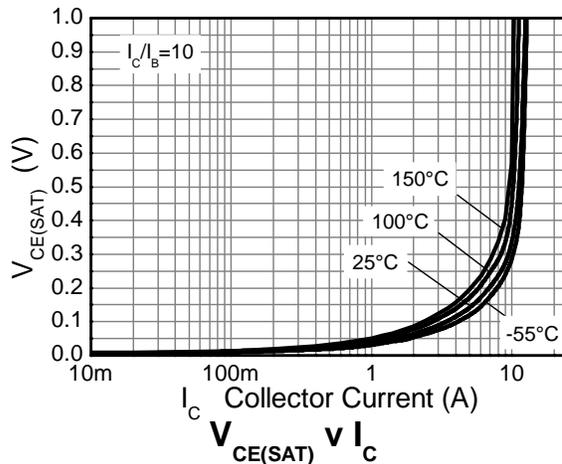
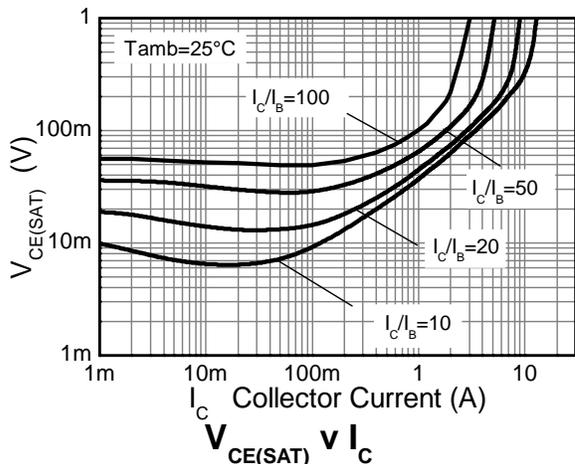


Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified)

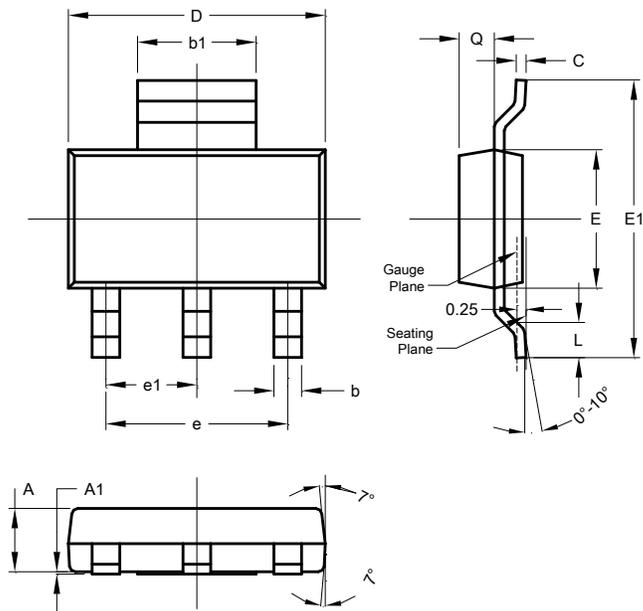
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	160	200	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	60	75	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{ECO}	6	7	—	V	$I_E = 100\mu\text{A}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.3	—	V	$I_E = 100\mu\text{A}$
Collector Cutoff Current	I_{CBO}	—	<1	50	nA	$V_{CB} = 160\text{V}$
Collector Cutoff Current	I_{CEX}	—	—	100	nA	$V_{CB} = 160\text{V}$, $R_{BE} < 1\text{k}\Omega$
Emitter Cutoff Current	I_{EBO}	—	<1	50	nA	$V_{EB} = 5.6\text{V}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{CE(sat)}$	—	37	50	mV	$I_C = 1\text{A}$, $I_B = 100\text{mA}$
		—	105	155		$I_C = 1\text{A}$, $I_B = 10\text{mA}$
		—	110	150		$I_C = 2\text{A}$, $I_B = 40\text{mA}$
		—	200	300		$I_C = 7\text{A}$, $I_B = 700\text{mA}$
Base-Emitter Saturation Voltage (Note 9)	$V_{BE(sat)}$	—	1,050	1,150	mV	$I_C = 7\text{A}$, $I_B = 700\text{mA}$
Base-Emitter Turn-on Voltage (Note 9)	$V_{BE(on)}$	—	960	1,050	mV	$I_C = 7\text{A}$, $V_{CE} = 2\text{V}$
DC Current Gain (Note 9)	h_{FE}	200	300	500		$I_C = 100\text{mA}$, $V_{CE} = 2\text{V}$
		160	220			$I_C = 2\text{A}$, $V_{CE} = 2\text{V}$
		25	40			$I_C = 7\text{A}$, $V_{CE} = 2\text{V}$
Transition Frequency	f_T	—	130	—	MHz	$V_{CE} = 10\text{V}$, $I_C = 50\text{mA}$, $f = 100\text{MHz}$
Input Capacitance	C_{ibo}	—	310	400	pF	$V_{EB} = 0.5\text{V}$, $f = 1\text{MHz}$
Output Capacitance (Note 9)	C_{obo}	—	19.7	25	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{ON}	—	40.5	—	ns	$V_{CC} = 10\text{V}$, $I_C = 500\text{mA}$, $I_{B1} = -I_{B2} = 50\text{mA}$
	t_{OFF}	—	772	—		

 Note: 9. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

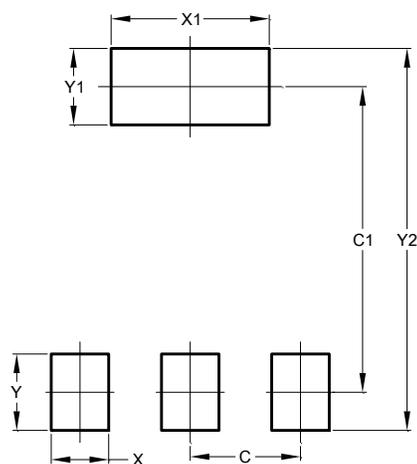


Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00